

(1) bonding a cap wafer to said substrate wafer with an adhesive layer;

(2) patterning and etching said cap wafer and said adhesive layer to form islands of layers of said cap wafer and said adhesive layer on said substrate wafer; and

(3) depositing and patterning at least one metal ~~and/or insulator~~ layer on said islands to form a sidewall around each of said islands.

2. (Previously presented)

The method of claim 1, further comprising the steps of:

(1) patterning and etching etch access holes in said cap wafer of said enclosures;

(2) removing said adhesive layer through said etch access holes from said enclosures; and

(3) sealing said etch access holes with deposited films.

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4. (Original) The method of claim 1, wherein said etching is accomplished with high-density plasma that contains hydrogen or argon.

5. (Original) The method of claim 1, wherein said substrate wafer comprises one or more of following:

micro-electro-mechanical device,

polymeric sacrificial layer,

polymeric planarizing layer,  
microelectronic circuit,  
and electrical component,  
prior to said bonding.

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6. (Previously presented)

The method of claim 1, further comprising a step of  
depositing getters on said cap wafer prior to said step (1)  
of bonding a cap wafer to said substrate wafer with an  
10 adhesive layer and subsequent heat activation of said  
getters.

7. (Previously presented)

The method of claim 2, wherein said deposited films  
15 comprises gas gettering materials.

8. (Currently amended)

The method of claim 7, wherein said gettering  
materials comprise ~~one or more of the following:~~

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$TiN_xO_y$  and/or

~~$TiZr_x$~~

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$TiN_x$

11. (Withdrawn)

The method of claim 2, wherein in said sealing is done  
under controlled gas pressure environment comprising high  
5 vacuum or inert gas.

12. (Withdrawn)

The method of claim 2, wherein said enclosures form  
pressure transducers.

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13. (Currently amended)

The method of claim 12, wherein said enclosures form  
vacuum or hermetic packaging for micro-electro-mechanical  
devices.

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14. (Original)

The method of claim 2, wherein said removing said  
adhesive layer is by etching with oxygenated plasma.

20 15. (Currently amended)

Said etching in claim 14 ~~further~~ removes ~~any~~ organic  
polymer coating or sacrificial layer ~~present~~ in said  
enclosures.

25 17. (Original)

The method of claim 1, wherein said depositing at  
least on metal layer is by physical vapor deposition,  
plating, electroplating, or chemical vapor deposition.

19. (Withdrawn)

The method of claim 1, further comprises planarizing  
said substrate wafer prior to said bonding, comprising  
5 steps of:

coating said wafer with a thick epoxy layer;  
curing said epoxy layer by heat or ultraviolet light; and  
thinning said epoxy layer to the desired thickness by  
lapping, grinding or polishing.

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20. (Withdrawn)

The method of claim 19, wherein said thick epoxy layer  
fills holes, cavities, troughs, or underside space of  
suspended structures.

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21. (Withdrawn)

The method of claim 20, further comprising the step of  
placing said wafer under a vacuum during or after said  
coating.

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28. (Original)

The method of claim 1, wherein said adhesive layer is  
disposed by spinning and said spinning is at speed of  
between 1500 rpm to 7000 rpm for less than 2 seconds.

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29. (Original)

The method of claim 1, wherein said adhesive layer comprises Abocast 50-24 epoxy resin from Abatron, Incorporated, Kenosha, WI 53144 USA.

- 5 30. (New) A plurality of sealed micro enclosures on a substrate wafer, each enclosure is enclosed by:
- (1) a top wafer bonded to said substrate wafer with an epoxy layer,
  - 10 (2) a bottom formed from said substrate wafer, and
  - (3) a sidewall formed from at least one metal films,
- wherein said metal films are prepared by sputtering or evaporation deposition processes, said sidewall surround an island on said substrate wafer, and said island is
- 15 formed from layers comprising said top wafer and said epoxy layer.

### **Conclusion**

This amendment is submitted in reply to the office

20 action dated 25 November 2005. The applicant respectfully request requests reconsideration and further examination of the patent application under 37 C. F. R. § 1.111.

Upon entry of the foregoing Amendment, claims 1-2, 4-8, 11-15, 17, 28 and 29 remain active in this office

25 action. Claim 30 is added as a new claim. The amendments

are believed to introduce no new matter, and their entry is respectfully requested.

Respectfully Submitted

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Chang-Feng Wan

Applicant, Inventor

16210 Shadybank Drive

10 Dallas, TX 75248